

High voltage fast-switching NPN power transistor

Datasheet - production data

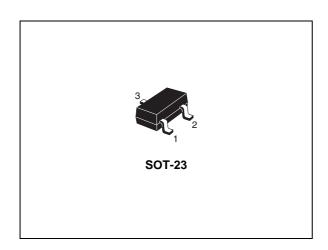
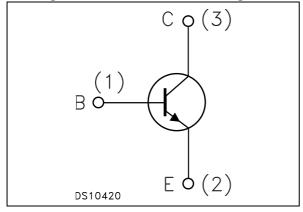


Figure 1. Internal schematic diagram



Features

- Excellent h_{FE} linearity up to 50 mA
- Miniature SOT-23 plastic package for surface mounting circuits
- Tape and reel packaging
- The PNP complementary type is STR2550

Applications

• LED driving

Description

This device is a high voltage fast-switching NPN power transistor, manufactured using diffused collector planar technology for high switching speeds.

It employs a base island structure with planar edge termination to enhance switching speeds, while maintaining a wide RBSOA.

Table 1. Device summary

Order code	Marking	Package	Packing
STR1550	1550	SOT-23	Tape and reel

Contents STR1550

Contents

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STR1550 Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage (I _E = 0)	500	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	500	V
V _{EBO}	Emitter-base voltage (I _C = 0)	9	V
I _C	Collector current	0.5	Α
I _{CM}	Collector peak current (t _P < 5 ms)	1	Α
P _{TOT}	Total dissipation at T _{amb} = 25 °C	500	mW
T _{STG}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJA} ⁽¹⁾	Thermal resistance junction-ambient max	250	°C/W

^{1.} Device mounted on PCB area of 1 cm².

Electrical characteristics STR1550

2 Electrical characteristics

 $T_{case} = 25$ °C unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I_{CBO} Collector cut-off current $(I_E = 0)$		V _{CB} = 500 V			10	μΑ
V _{(BR)CBO} Collector-base breakdown voltage (I _E = 0)		I _C = 100 μA	500			V
V _{(BR)CEO} (1) Collector-emitter breakdown voltage (I _B = 0)		I _C = 1 mA	500			V
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = 100 μA	12			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 20 \text{ mA}, I_B = 2 \text{ mA}$			0.2	V
VCE(sat)		$I_C = 50 \text{ mA}, I_B = 6 \text{ mA}$			0.3	V
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	I _C = 50 mA, I _B = 5 mA			0.9	V
V _{BE(on)} Base-emitter on voltage		I _C = 50 mA, V _{CE} = 10 V			0.9	V
h _{FE} ⁽¹⁾	DC current gain	I _C = 1 mA, V _{CE} = 10 V	100			
		$I_C = 50 \text{ mA}, V_{CE} = 10 \text{ V}$	100		300	
		$I_C = 100 \text{ mA}, V_{CE} = 10 \text{ V}$	10			

^{1.} Pulse test: pulse duration ≤ 300 µs, duty cycle ≤ 2%

-55°C

100°C

0.1

Ic(A)

AM17433v1

2.1 Electrical characteristics (curves)

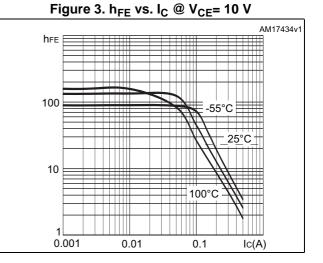


hfe

100

10

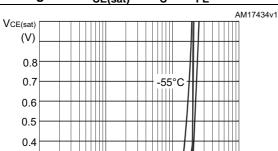
0.001



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0.01

Figure 4. $V_{CE(sat)}$ vs. I_C @ h_{FE} = 5



25°C

Ic(A)

Ic(A)

100°C

0.1

0.1

Figure 5. $V_{CE(sat)}$ vs. I_C @ h_{FE} = 10

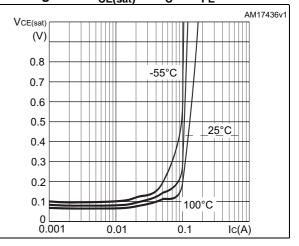


Figure 6. $V_{BE(sat)}$ vs. I_C @ h_{FE} = 5

0.01

0.3

0.2

0.001

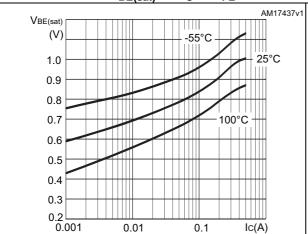


Figure 7. $V_{BE(sat)}$ vs. I_C @ h_{FE} = 10

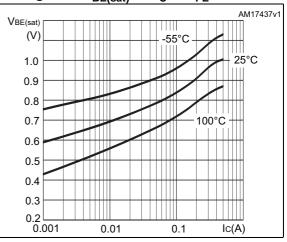
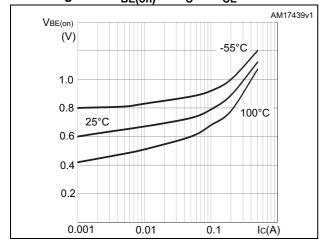


Figure 8. $V_{BE(on)}$ vs. $I_C @ V_{CE}$ = 10 V

0.01



3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

e1

e1

E

S

CAUSE PLANE

S

GOSS3390

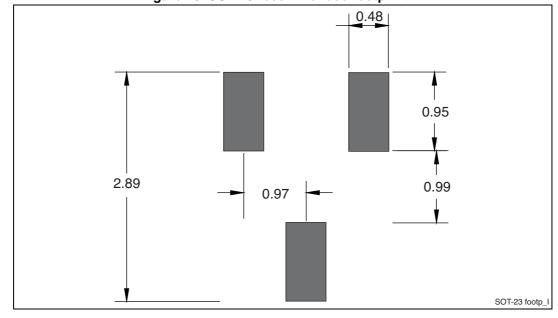
Figure 9. SOT-23 drawings

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Table 5. SOT-23 mechanical data

Dim.	mm			
	Min.	Тур.	Max.	
А	0.89		1.40	
A1	0		0.10	
В	0.30		0.51	
С	0.085		0.18	
D	2.75		3.04	
е	0.85		1.05	
e1	1.70		2.10	
E	1.20		1.75	
Н	2.10		3.00	
L		0.60		
S	0.35		0.65	
L1	0.25		0.55	
а	0°		8°	

Figure 10. SOT-23 recommended footprint (a)



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a. Dimensions are in mm.

Revision history STR1550

4 Revision history

Table 6. Document revision history

Date	Revision	Changes
17-Oct-2011	1	Initial release
05-Jun-2012	2	Modified: features, <i>Table 4</i> (V _{CE(sat)} values, h _{FE} test conditions and values)
21-May-2013	3	 Modified: Table 4 (V_{BE(sat)} values, h_{FE} max. value and V_{(BR)EBO} min. value Inserted: V_{BE(on)} Modified: Table 4 (h_{FE} max. value) Added new section: Electrical characteristics (curves)
27-May-2013	4	Document status promoted from preliminary to production data
09-May-2014	5	Updated Table 1: Device summary and Section 3: Package mechanical data

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